

CLAIM AMENDMENTS

Please cancel Claims 13-43, amend Claim 1 and add new Claim 47 as follows:

1. (Currently Amended) A process for producing a crystalline thin film by melting and resolidifying a thin film, comprising the steps of:
 - (A) preparing a thin film having a specific region arranged at a predetermined position, the specific region being continuous to a surrounding non-specific region and different in melting or resolidification property from the surrounding non-specific region, wherein the thin film is provided on a non-crystalline substrate;
 - (B) locally melting and resolidifying a partial area including the specific region in the thin film; and
 - (C) locally melting and resolidifying another partial area including a non-specific region sharing a common boundary with an area crystallized by resolidification in a preceding step.

2. (Original) The process for producing a crystalline thin film according to Claim 1, wherein the step (C) is repeated while shifting the area to be locally molten in one direction, whereby the crystallized area is made to grow in the direction of shifting.

3. (Original) The process for producing a crystalline thin film according to Claim 2, wherein the step (A) is a step of preparing a thin film in which a plurality of specific regions are aligned in line, the step (B) is a step of melting and resolidifying an area including two or more specific regions among the plurality of specific regions, and the step (C) is repeated while shifting the area to be locally molten in a direction almost orthogonal to a direction along which the plurality of specific regions are aligned.

4. (Original) The process for producing a crystalline thin film according to Claim 2, wherein the step (A) is a step of preparing a thin film in which a plurality of specific regions are aligned in line, and the step of (C) is repeated while shifting the area to be locally molten in a direction along which the plurality of specific regions are aligned.

5. (Original) The process for producing a crystalline thin film according to Claim 1, wherein the step of (B) is a step of locally melting the non-specific region, and continuously shifting the molten area to make the molten area pass through the specific region, thereby melting and resolidifying the specific region.

6. (Original) The process for producing a crystalline thin film according to Claim 1, wherein the step (C) is carried out while continuously shifting the molten area subsequently to the preceding step.

7. (Original) The process for producing a crystalline thin film according to Claim 2, wherein the step (C) is repeated while continuously shifting the area to be locally molten in one direction, whereby the crystallized area is made to grow in the direction of shifting.

8. (Original) The process for producing a crystalline thin film according to Claim 1, wherein the step (C) is a step in which the partial area is locally heated pulsewise, and molten and resolidified.

9. (Original) The process for producing a crystalline thin film according to Claim 8, wherein the step (C) is repeated while shifting stepwise the area to be locally molten in one direction, whereby the crystallized area is made to grow in the direction of shifting.

10. (Original) The process for producing a crystalline thin film according to Claim 8, wherein in the step (C), the area to be molten includes a part of the area crystallized in the preceding step.

11. (Original) The process for producing a crystalline thin film according to Claim 8, wherein in the step (C) that is repeatedly carried out, the area to be molten includes an area that is not yet molten and resolidified.

12. (Original) The process for producing a crystalline thin film according to Claim 1, wherein a spatial position of the specific region in the thin film is controlled, whereby a spatial position of at least a part of the crystal grain having a continuous crystal structure in the crystalline thin film is controlled.

13.-43. (Cancelled)

44. (Original) An element formed by using the crystalline thin film obtained in the process of Claim 1, wherein a spatial position of at least a part of a crystal grain having a continuous crystal structure is determined by a spatial position of a specific region in a starting thin film, and a crystal grain having the controlled spatial position is used in an active region.

45. (Original) The element according to Claim 44, wherein the active region is formed in a single crystal grain of the crystalline thin film.

46. (Original) A circuit comprising a plurality of elements of Claim 45, wherein the elements are connected to one another by a wire.

47. (New) The process for producing a crystalline thin film according to Claim 1, wherein the non-crystalline substrate is one selected from the group consisting of a quartz substrate, a glass substrate, and a plastic film.